

PATTERN FORMING METHOD

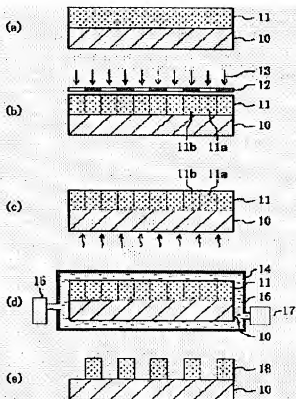
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Abstract of JP2003035961

PROBLEM TO BE SOLVED: To prevent pattern falling in a resist pattern.

SOLUTION: A resist film 11 comprising a chemical amplification type resist material having a base polymer containing fluorine atoms and a hydrophilic group, a crosslinker and an acid generator is formed and patternwise exposed by irradiation with F2 laser light 13 through a photomask 12. The patternwise exposed resist film 11 is developed in a supercritical fluid 16 to form the objective resist pattern 18 comprising the unexposed regions 11b of the resist film 11.



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